

ESD Protection Diode

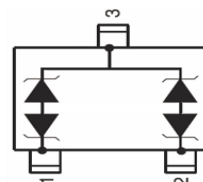
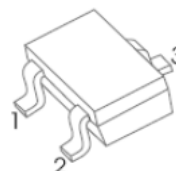
FEATURES

- Ultra low leakage: nA level.
- Low clamping voltage.
- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

APPLICATIONS

- CAN bus protection
- Automotive applications

SOT-323



DEVICE MARKING AND ORDERING INFORMATION

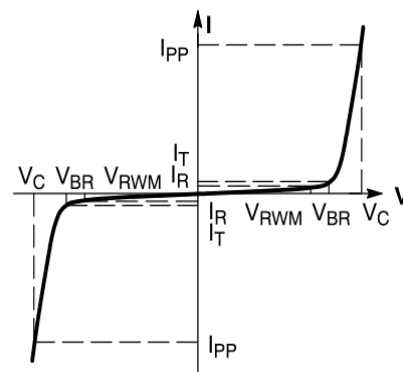
Device	Marking	Shipping
ESDSOT24B	24B	3000/Tape&Reel

MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
IEC 61000-4-2 (ESD) Contact		±30	kV
Air		±30	
peak pulse power@8/20 μs	PPP	250	W
peak pulse current @8/20 μs	IPP	7	A
Storage Temperature Range	Tstg	-55 ~ +150	°C
Operating Temperature Range	TJ	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

Symbol	Parameter
IPP	Maximum Reverse Peak Pulse Current
VC	Clamping Voltage @ IPP
VRWM	Working Peak Reverse Voltage
IR	Maximum Reverse Leakage Current @ VRWM
VBR	Breakdown Voltage @ IT
IT	Test Current
IF	Forward Current
VF	Forward Voltage @ IF
Ppk	Peak Power Dissipation
C	Capacitance @ VR = 0 and f = 1.0 MHz



ELECTRICAL CHARACTERISTICS (Ta= 25°C)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
reverse stand-off voltage	VRWM	-	-	24	V
reverse leakage current (VRWM = 24 V, Pin 1、2 to Pin 3) (VRWM = 24 V, Pin 3 to Pin 1、2)	IRM	-	-	200 200	nA
breakdown voltage (IT = 1 mA, Pin 1、2 to Pin 3) (IT = 1 mA, Pin 3 to Pin 1、2)	VBR	26.2	-	32	V
Clamping Voltage (IPP = 5A (8 x 20μs pulse))	VC	-	-	40	V
Clamping Voltage (IPP = 7A (8 x 20μs pulse))	VC	-	-	44	V
Junction Capacitance (VR = 0V, f = 1MHz)	CJ	-	30	-	pF

Typical Characteristics

Fig. 1 - 8 X 20 μ s Pulse Waveform

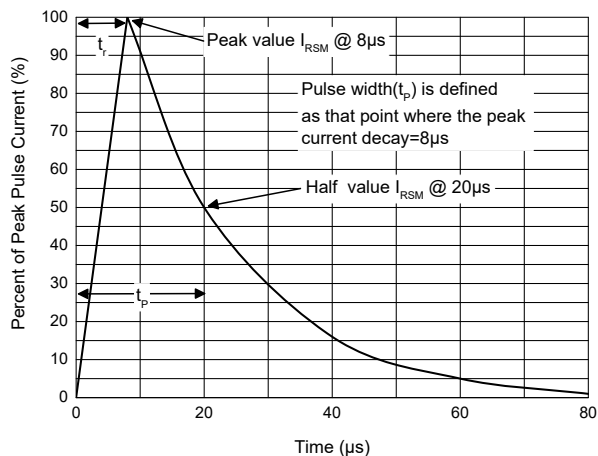


Fig. 2 - Capacitance Characteristics

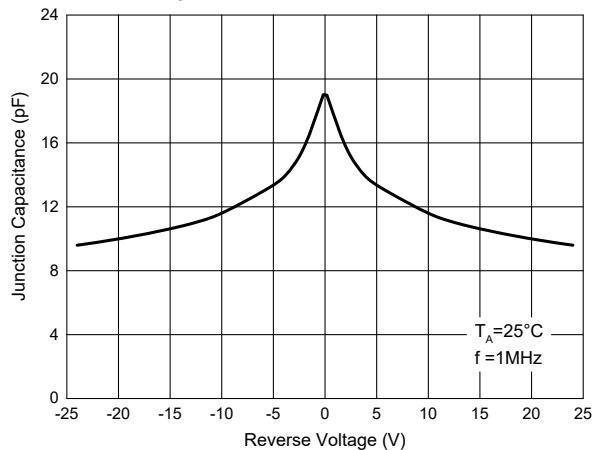


Fig. 3 - Clamping Voltage Characteristics

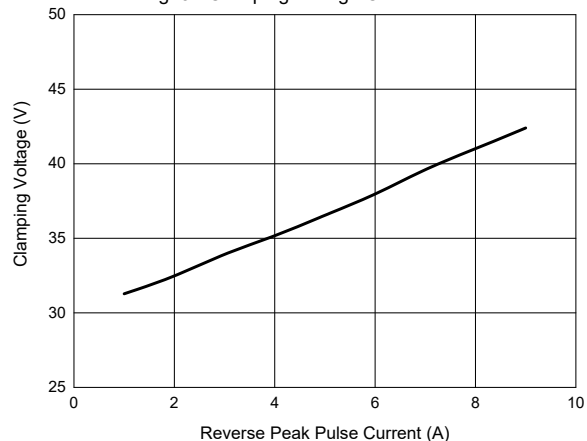


Fig. 4 - TLP Measurement

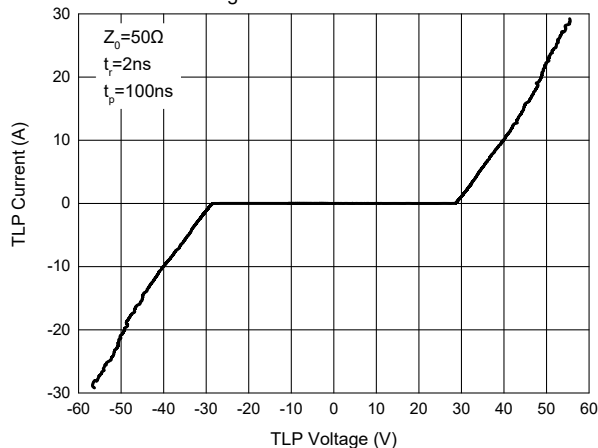


Fig.5: Typical Reverse Characteristics

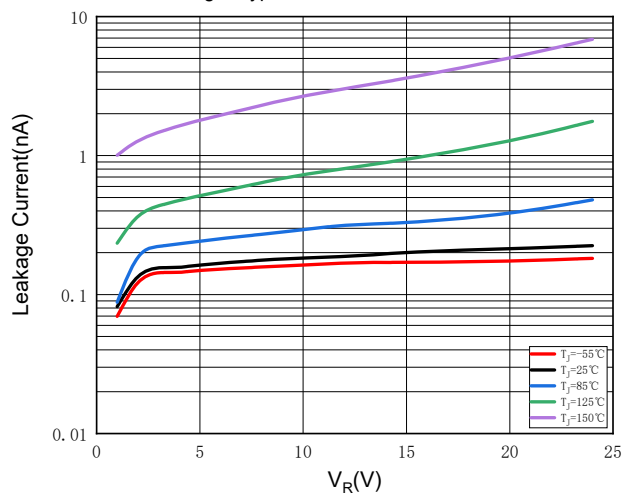


Fig. 6 - Pulse Derating Curve

